

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT-AND-TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1531		SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.			
				FILING DATE Filed Herewith		GROUP	
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
AA							
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
AB							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
K.N.	AC		Abstract of: Oxidation of Sintered Aluminum Nitride at Near-ambient temperatures; Dutta, I.; Mitra, S. ; Rabenberg, L.; Journal of the American Ceramic Society, Vol. 75, No. 11, pp. 3149-53, Nov. 1992				
	AD		Abstract of: Oxidation of lead films by rf sputter etching in an oxygen plasma; J.H. Greiner				
	AE		Abstract of: Josephson Tunneling Barriers by rf Sputter Etching in an Oxygen Plasma; J.H. Greiner; Journal of Applied Physics; Vol. 42; Number 12; November 1971				
	AF		Abstract of: Measurement of Tunnel Current Density in a Metal Oxide Metal System as a Function of Oxide Thickness; J.M. Eldridge and J. Matisoo				
	AG		Abstract of: Optical Measurement of Film Growth on Silicon and Germanium Surfaces in Room Air; R.J. Archer				
	AH		Preparation of Al-O-N Films by Electron Cyclotron Resonance Plasma-Assisted Chemical Vapor Deposition; Takashi Goto; Wei Zhang; Toshio Hirai, 1999 Publication Board, Japanese Journal of Applied Physics; Vol. 38 (1999) Pt. 1, No. 6A; pp. 3668-74				
	AI		Ion assisted deposition of oxynitrides of aluminum and silicon; G.A. Al-Jumaily and T.A. Mooney; W.A. Spurgeon and H.M. Dauplaise				
K.N.	AJ		Abstract of: Preparation of aluminum nitride and oxynitride thin films by ion-assisted deposition; Targove, J.D.; Lingg, L.J.; Lehan, J.P. et al.; Conference: Materials Modification and Growth Using Ion Beams Symposium, pp. 311-16; Mater. Res. Soc., Pittsburgh, PA 1987				
EXAMINER <i>Khuemnguyen</i>				DATE CONSIDERED <i>08/16/02</i>			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

EL 465852887

 JC675 U.S. PTO
 09/155673
 01/05/01

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT-AND-TRADEMARK-OFFICE		ATTY. DOCKET NO. MI22:1531		SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.			
				FILING DATE Filed Herewith		GROUP	
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA						
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	AB						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
K.N.	AC		Film Synthesis and Growth Using Energetic Beams; Material Research Society Symposium Proceedings Vol. 388; April 17-20, 1995 San Francisco, CA				
	AD		Some Properties of Chemically Vapor Deposited Films of $Al_2O_3N_3$ on Silicon; E.A. Irene, V.J. Silvestri and G.R. Woolhouse; Journal of Electronic Materials, Vol. 4, No. 3, 1975; pp. 409-427				
	AE		Chemical Vapor Deposition of $Al_2O_3N_3$ Films; V.J. Silvestri, E.A. Irene, S. Zirinsky; J.D. Kuptsis; Journal of Electronic Materials, Vol. 4, No. 3, 1975; pp. 429-444				
	AF		Disk hydrogen plasma assisted chemical vapor deposition of aluminum nitride; T.Y. Sheng, Z.Q. Yu, and G.J. Collins; Appl. Phys. Lett. 52(7), February 1988; pp. 576-578				
	AG		Epitaxial Growth of Aluminum Nitride on Sapphire and Silicon; K. Dovidenko; S. Oktyabrsky; J. Narayan; and M. Razeghi; Mat. Res. Soc. Symp. Proc. Vol. 358; 1995 Materials Research Society; pp. 1023-1028				
	AH		III-Nitride, SiC and Diamond Materials for Electronic Devices; Materials Research Society, Symposium Proceedings Vol. 423; April 8-12, 1996, San Francisco, CA; pp. 667-672				
	AI		Electrochemical Behaviour of AlN Films Prepared by Reactive Cathodic Sputtering; F. Vacandio, Y. Massiani, P. Gravier, L. Fedrizzi and D. Brida; Materials Science Forum; Vols. 289-292 (1998) pp. 689-697; 1998 Trans Tech Publications, Switzerland				
K.N.	AJ		Measurement of stress distribution in Si_3N_4 using AlN thin films; M. Akiyama, C.N. Xu, K. Nonaka, T. Watanabe; Journal of Materials Science Letters (1998) pp. 2093-2095				
EXAMINER <i>K. Khemnguyen</i>				DATE CONSIDERED <i>08/16/02</i>			
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>							

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1531	SERIAL NO. Filed Herewith		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.			
				FILING DATE Filed Herewith	GROUP		
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes No
	AC						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
K.N.	AD		Changes in optical transmittance and surface morphology of AlN thin films exposed to atmosphere; Yoshihisa Watanabe, Yoshifumi Sakuragi, Yoshiki Amamoto, and Yoshikazu Nakamura; J. Mater. Res., Vol. 13, No. 10, Oct. 1998; 1998 Materials Research Society; pp. 2956-61				
	AE		Optical Interference Coatings; Florin Abeles, Chair/Editor; Proceedings Europto Series; SPIE Vol. 2253; part 2 of 2; pp. 1275-85				
	AF		Tunneling Leakage Current in Ultrathin (<4nm) Nitride/Oxide Stack Dielectrics; Ying Shi; Xiewen Wang; T.P. Ma; IEEE Electron Device Letters, Vol. 19, No. 10, October 1998; pp. 388-390				
	AG		High Quality Ultra-thin (1.5 nm) TiO ₂ /Si ₃ N ₄ Gate Dielectric for Deep Sub-micron CMOS Technology; Xin Guo, Xiewen Wang; Sijiong Luo, T.P. Ma, and T. Tamagawa; Dept. of Electrical Engineering, Yale University, New Haven, CT 06520				
	AH		High Quality Ta ₂ O ₅ Gate Dielectrics with T _{ox,eq} < 10Å; H. F. Luan, S.J. Lee, C.H. Lee, S.C. Song, Y.L. Mao, Y. Senzaki, D. Roberts and D.L. Kwong				
	AI		Abstract of: Low interface trap density for remote plasma deposited SiO ₂ /sub 2/ on n-type GaN; Applied Physics Letters, Vol. 68, No. 13; pp. 1850-2				
K.N.	AJ		Abstract of: Interface-state characteristics of GaN/GaAs MIS capacitors; Solid-State Electronics, vol. 25, no. 8, pp. 811-15				
EXAMINER <i>Khiem Nguyen</i>				DATE CONSIDERED <i>08/16/02</i>			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1531		SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.			
				FILING DATE Filed Herewith		GROUP	
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
AA							
FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
AB							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
K.N.	AC		Applications of Aluminium Nitride Films Deposited by Reactive Sputtering to Silicon-on-Insulator Materials; Stefan Bengtsson, Mats Bergh, Manolis Choumas, Christian Olesen and Kjell O. Jeppson; Jpn. J. Appl. Phys. Vol. 35 (1996) Pt. 1, No. 8; pp. 4175-81				
K.N.	AD		Characteristics of AlN Thin Films Deposited by Electron Cyclotron Resonance Dual-Ion-Beam Sputtering and their Application to GHz-Band Surface Acoustic Wave Devices; Hiroshi Okano, Naoki Tanaka, Yasuhiro Hirao, Yasumi Kobayashi, Kenichi Shibata and Shoichi Nakano; Jpn. J. Appl. Phys. Vol. 33 (1994); Pt. 1, No. 5B; pp. 2957-2961				
K.N.	AE		An Aluminum Oxynitride Film; Wang Dehuang, Guo Liang; Thin Solid Films, 198 (1991) pp. 207-210				
K.N.	AF		Formation of aluminum oxynitride diffusion barriers for Ag metallization; Y. Wang and T. L. Alford; Applied Physics Letters; Vol. 74, No. 1; 4 January 1999; American Institute of Physics; pp. 52-54				
K.N.	AG		Abstract of: Simulation of Hyperthermal deposition of Si and C on SiC surfaces; Applied Physics Letters; Vol. 74, No. 1; 4 January 1999; 1999 American Institute of Physics				
K.N.	AH		Nitrogen plasma source ion implantation for corrosion protection of aluminum 6061-T4; J. H. Booske, L. Zhang, W. Wang, K. Mente, N. Zjaba, C. Baum, and J.L. Shohet; J. Mater. Res. Vol. 12, No. 5, May 1997; 1997 Materials Research Society; pp. 1356-66				
K.N.	AI		Thickness measurement of submonolayer native oxide films on silicon wafers; Fuhe Li, Marjorie K. Balazs, Bruce E. Deal; Wafers & Substrates; Solid State Technology, February 2000; pp. 87, 88, 92, 94, 96, 98				
K.N.	AJ		Electrical Conduction and Dielectric Breakdown in Aluminum Oxide Insulators on Silicon; James Kolodzey et al.; IEEE Transactions on Electron Devices; Vol. 47, No. 1, January 2000; pp. 121-128				
EXAMINER			DATE CONSIDERED				
Khemenguyen			08/16/02				
*EXAMINER: Initial if reference considered, whether by not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form-PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1531	SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.		
				FILING DATE Filed Herewith	GROUP	
U.S. PATENT DOCUMENTS						
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
AA						
FOREIGN PATENT DOCUMENTS						
	Document Number	Date	Country	Class	Subclass	Translation
						Yes No
AB						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)						
K.N.	AC		Structural, Optical and Electronic Properties of Oxidized AlN Thin Films at Different Temperatures; Enam Ahmed Chowdhury et al.;			
	AD		Formation of Al-nitride films at room temperature by nitrogen ion implantation into aluminum; N. Lieske and R. Hezel; J. Appl. Phys. 52(9), Sept. 1981; pp. 5806-5810			
	AE					
	AF					
	AG					
	AH					
	AI					
K.N.	AI					
EXAMINER <i>K. Hennig</i>			DATE CONSIDERED <i>08/16/02</i>			
*EXAMINER: Initial if reference considered whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						